



US007095062B2

(12) **United States Patent**
Linthicum et al.

(10) **Patent No.:** **US 7,095,062 B2**
(45) **Date of Patent:** ***Aug. 22, 2006**

(54) **METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS ON SUBSTRATES INCLUDING NON-GALLIUM NITRIDE POSTS, AND GALLIUM NITRIDE SEMICONDUCTOR STRUCTURES FABRICATED THEREBY**

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.

This patent is subject to a terminal disclaimer.

(21) Appl. No.: **11/074,485**

(22) Filed: **Mar. 8, 2005**

(65) **Prior Publication Data**

US 2005/0161702 A1 Jul. 28, 2005

Related U.S. Application Data

(63) Continuation of application No. 10/115,354, filed on Apr. 3, 2002, now Pat. No. 6,864,160, which is a continuation of application No. 09/501,051, filed on Feb. 9, 2000, now Pat. No. 6,403,451.

(51) **Int. Cl.**

H01L 29/12 (2006.01)

(52) **U.S. Cl.** **257/103; 257/627; 257/21.125**

(58) **Field of Classification Search** 438/22-47,
438/479-509; 257/103, 618-628, E33.025,
257/E33.03

See application file for complete search history.

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